

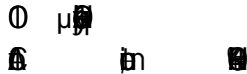


## CNY17-X Series

Rev.A.1.0

The CNY17-X series combine an AlGaAs infrared emitting diode as the emitter which is oasc(c)4 (upli)6 dec

Storage Temperature	T <sub>stg</sub>	-55+ 150	
Soldering Temperature	T <sub>sol</sub>	260	



(Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA	-	1.27	1.4	V
			I <sub>F</sub> =20mA	-	1.33	1.5	
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> =6V	-	-	1	μA
	Input Capacitance	C <sub>in</sub>	V=0, f=1MHz	-	10	-	pF
Output	Collector-Emitter dark current	I <sub>CEO</sub>	V <sub>CE</sub> =20V, I <sub>F</sub> =0	-	-	100	nA
	Collector-Emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> =0.1mA I <sub>F</sub> =0	80	-	-	V
	Collector-Base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> =0.1mA I <sub>F</sub> =0	80	-	-	V
	Emitter-Collector breakdown voltage	BV <sub>ECO</sub>	I <sub>E</sub> =0.1mA I <sub>F</sub> =0	7	-	-	V
	Emitter-Base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> =0.1mA I <sub>F</sub> =0	7	-	-	V
	DC Forward current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =0.5mA	100	-	600	-
	Current transfer ratio	CTR	I <sub>F</sub> =10mA V <sub>CE</sub> =5V	40	-	320	%

Transfer Characteristics



**FIG.1:** Forward Current vs. Ambient Temperature

**FIG.2:** Collector Power Dissipation vs. Ambient Temperature



FIG.13: Test Circuits of Response Time

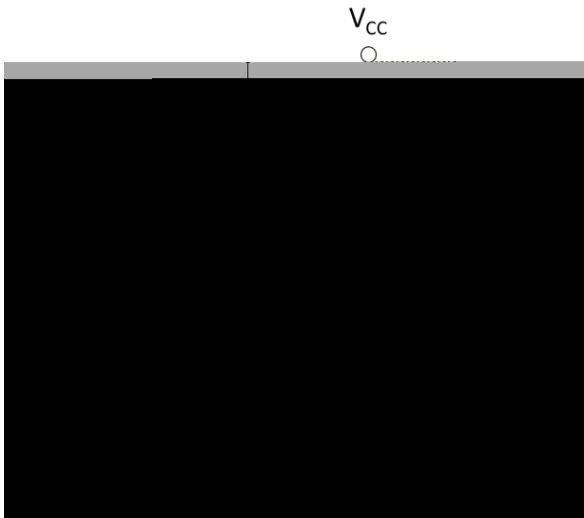
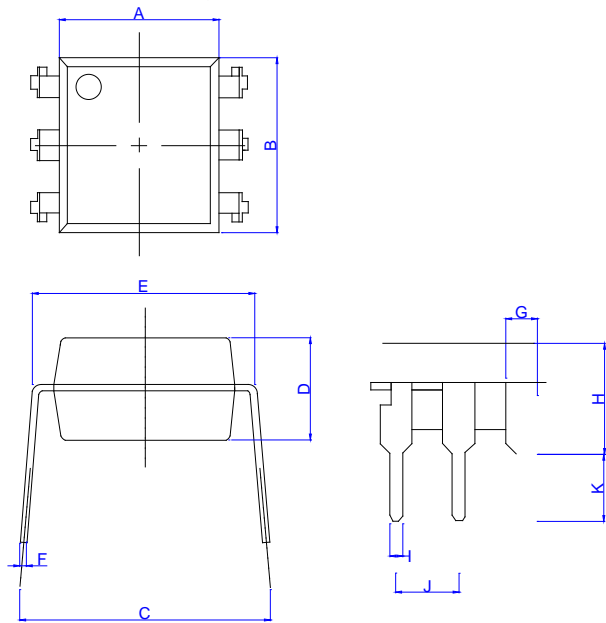


FIG.14: Curves of Response Time



FIG.15: Test Circuits of Frequency Response

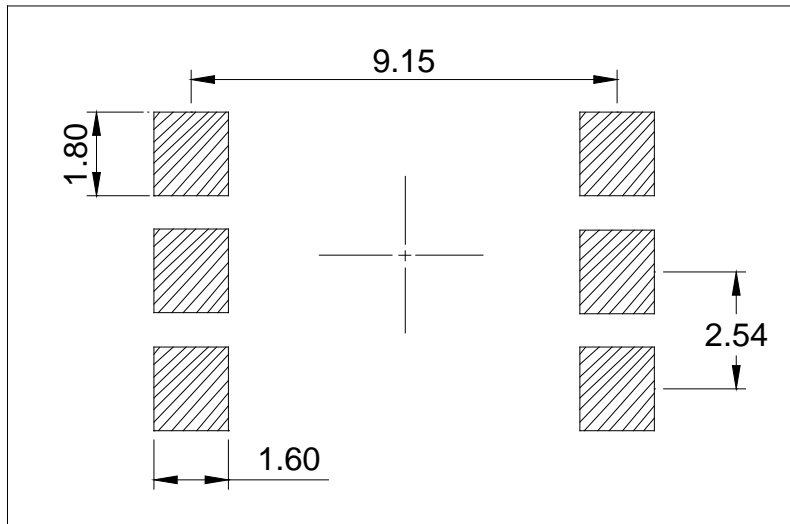
Standard DIP Type:



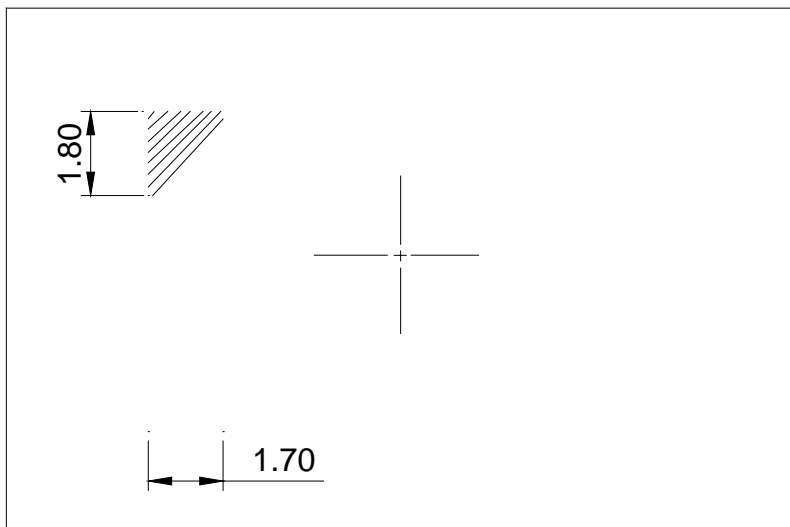
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.00		7.00	0.237		0.277
B	6.62		7.62	0.262		0.301
C	7.10		10.16	0.281		0.402
D	3.00		4.00	0.119		0.158
E	7.32		7.92	0.289		0.313
F						
G	0.90		1.50	0.036		0.059
H	3.50		4.80	0.138		0.190
I						
J						
K						



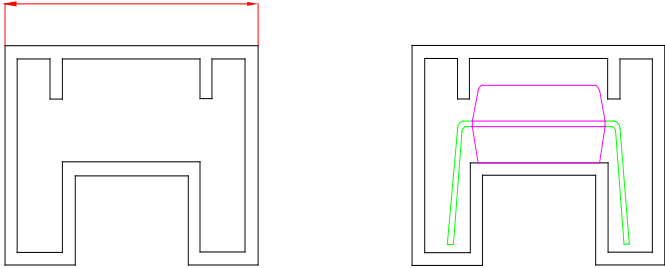
Option S

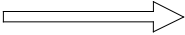
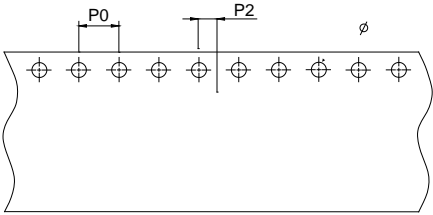


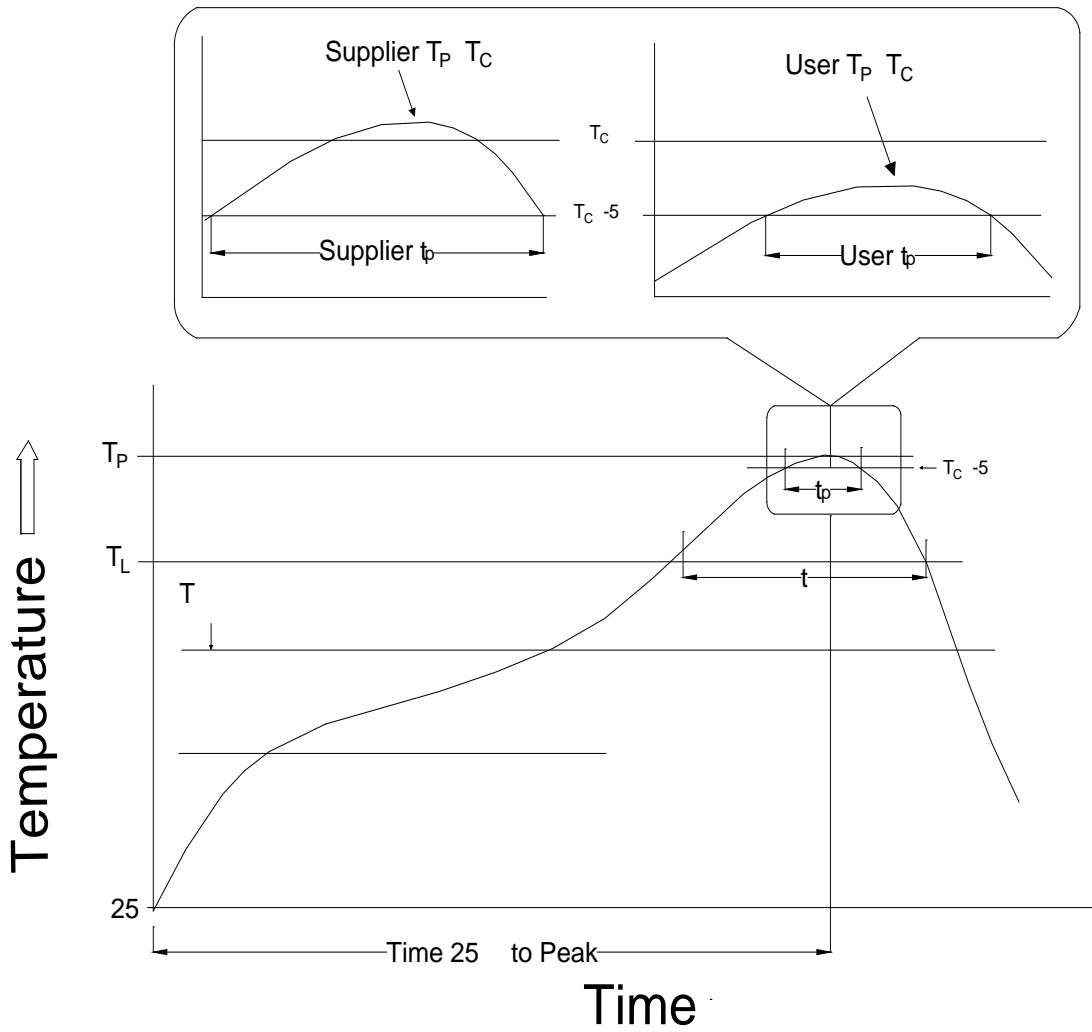
Option SL



Standard DIP










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